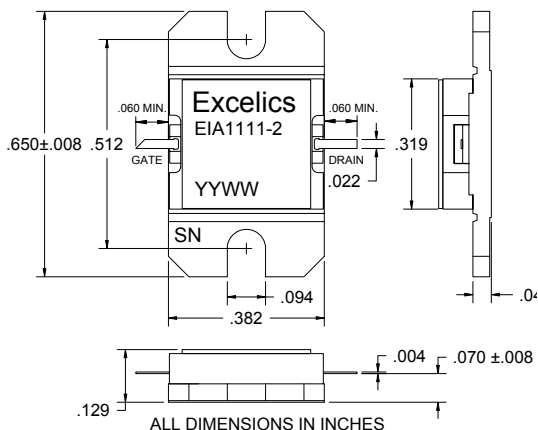


FEATURES

- 11.0– 11.5GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +34.0 dBm Output Power at 1dB Compression
- 11.0 dB Power Gain at 1dB Compression
- 32% Power Added Efficiency
- Hermetic Metal Flange Package



ELECTRICAL CHARACTERISTICS (T_a = 25°C)



Caution! ESD sensitive device.

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P_{1dB}	Output Power at 1dB Compression V _{DS} = 8 V, I _{DSQ} ≈ 800mA f = 11.0-11.5GHz	33.0	34.0		dBm
G_{1dB}	Gain at 1dB Compression V _{DS} = 8 V, I _{DSQ} ≈ 800mA f = 11.0-11.5GHz	10.0	11.0		dB
ΔG	Gain Flatness V _{DS} = 8 V, I _{DSQ} ≈ 800mA f = 11.0-11.5GHz			±0.6	dB
PAE	Power Added Efficiency at 1dB Compression V _{DS} = 8 V, I _{DSQ} ≈ 800mA f = 11.0-11.5GHz		32		%
I_{d1dB}	Drain Current at 1dB Compression f = 11.0-11.5GHz		900	1100	mA
I_{DSS}	Saturated Drain Current V _{DS} = 3 V, V _{GS} = 0 V		1400	1800	mA
V_P	Pinch-off Voltage V _{DS} = 3 V, I _{DS} = 14 mA		-1.0	-2.5	V
R_{TH}	Thermal Resistance ³		10	11	°C/W

Note: 1) Tested with 100 Ohm gate resistor.

2) S.C.L. = Single Carrier Level.

3) Overall R_{th} depends on case mounting.

ABSOLUTE MAXIMUM RATING^{1,2}

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²
V_{ds}	Drain-Source Voltage	12	8V
V_{gs}	Gate-Source Voltage	-5	-3V
I_{gsf}	Forward Gate Current	21.6mA	7.2mA
I_{gsr}	Reserve Gate Current	-3.6mA	-1.2mA
P_{in}	Input Power	32.5dBm	@ 3dB Compression
T_{ch}	Channel Temperature	175 °C	175 °C
T_{stg}	Storage Temperature	-65 to +175 °C	-65 to +175 °C
P_t	Total Power Dissipation	13W	13W

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.

Specifications are subject to change without notice.

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Revised February 2006